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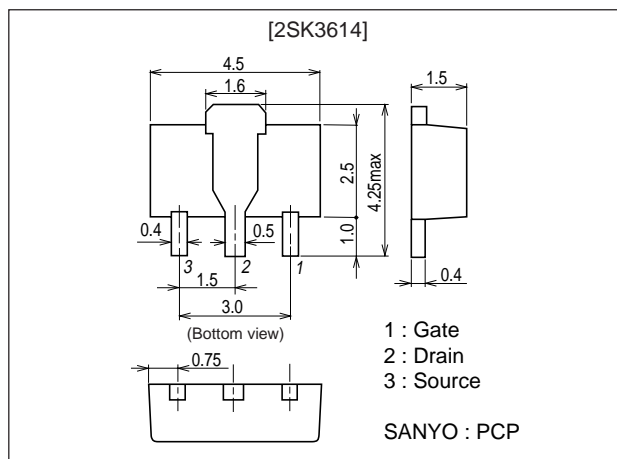
## 2SK3614 — N-Channel Silicon MOSFET — UltraHigh-Speed Switching Applications

### Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

### Package Dimensions

unit : mm  
2062A



### Specifications

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		60	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		4	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	16	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (250mm <sup>2</sup> ×0.8mm)	1.5	W
		T <sub>c</sub> =25°C	3.5	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0	60			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =2A	2	3.6		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =2A, V <sub>GS</sub> =10V		110	145	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =2A, V <sub>GS</sub> =4V		150	215	mΩ

Marking : LK

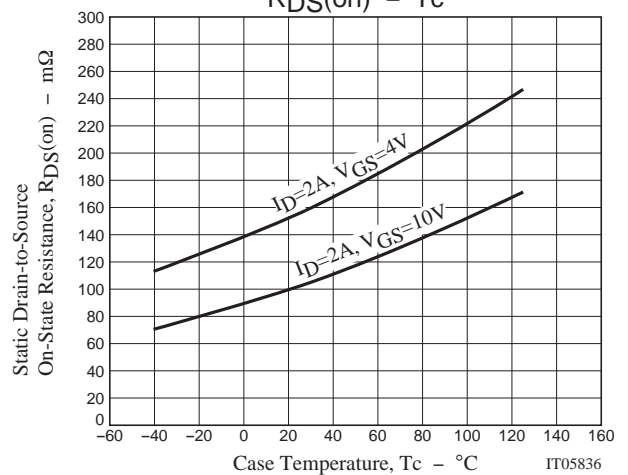
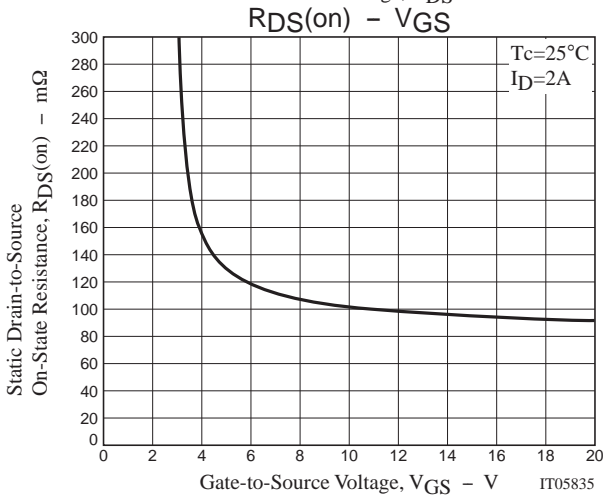
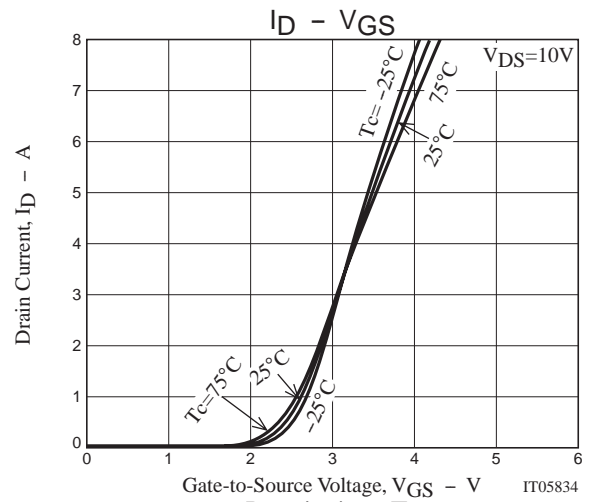
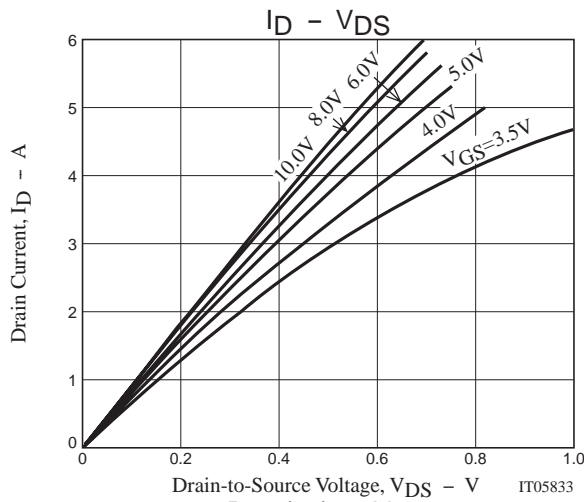
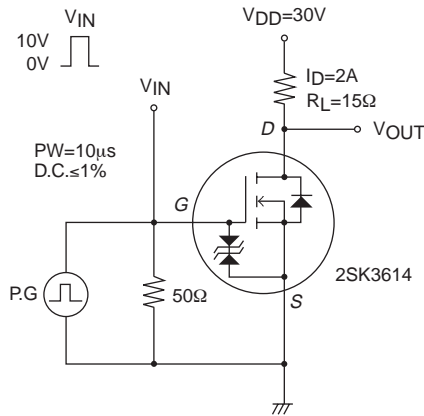
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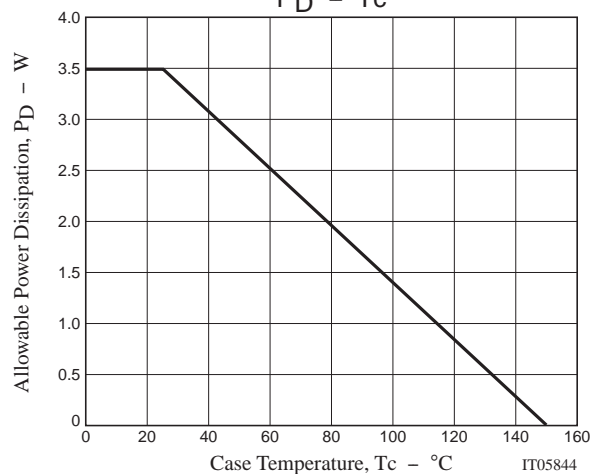
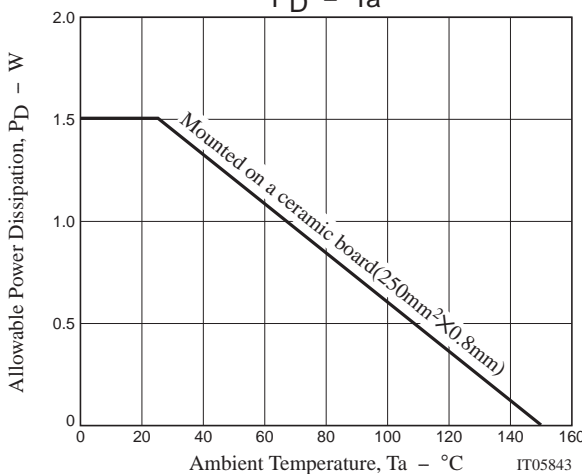
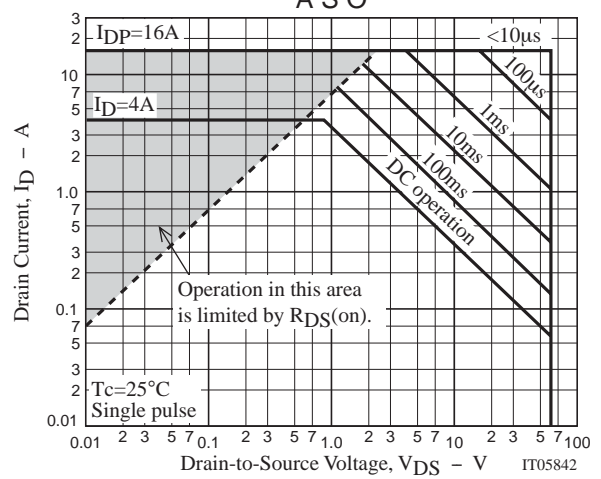
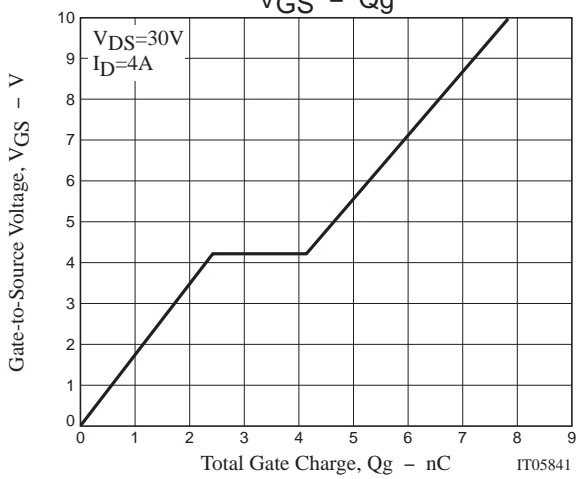
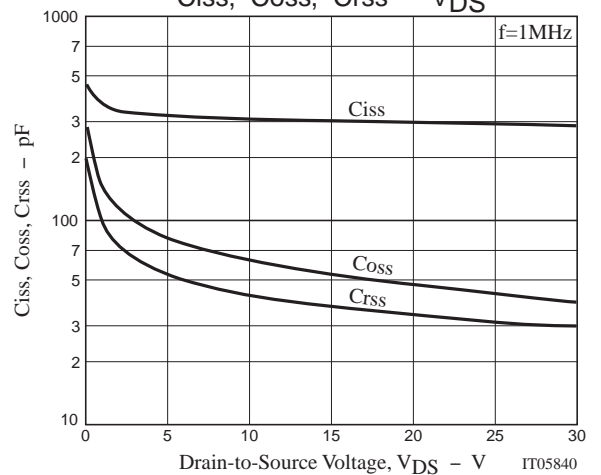
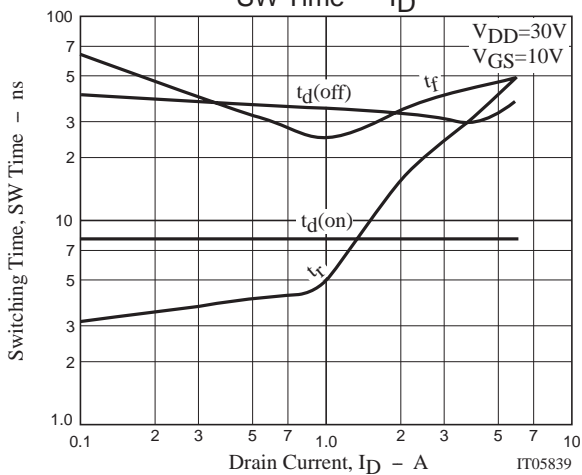
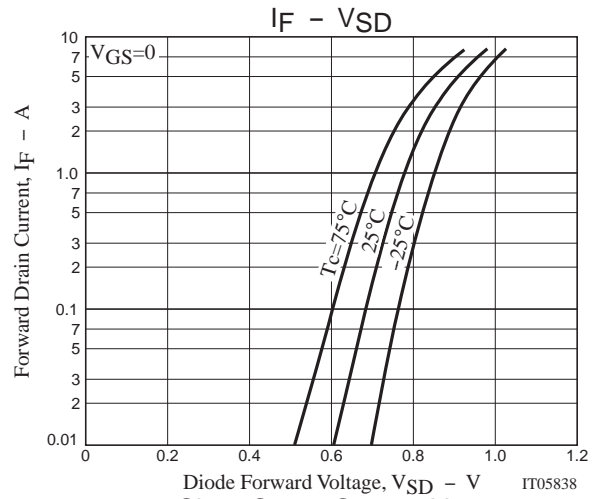
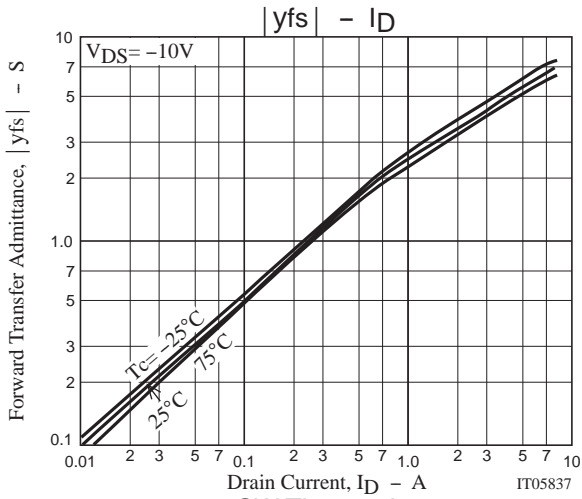
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V <sub>DS</sub> =20V, f=1MHz		300		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		54		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =20V, f=1MHz		34		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		8		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		16		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit.		32		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit.		34		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =4A		7.8		nC
Gate-to-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =4A		2.4		nC
Gate-to-Drain "Miller" Charge	Q <sub>gd</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =4A		1.7		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =4A, V <sub>GS</sub> =0	0.86		1.2	V

## Switching Time Test Circuit



# 2SK3614



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